A Method Of Forming A Metal Contact And Passivation Of A Semiconductor Feature

ABSTRACT

A method of forming a metal contact and passivation of a semiconductor feature, and devices made using the method. The method comprises the steps of forming a dielectric mask on a semiconductor substrate utilising photolithography processes; etching the semiconductor substrate such that one or more features are formed underneath respective portions of the dielectric mask; depositing a passivation layer on the substrate with the dielectric mask in place above the features; subjecting the substrate to an etchant such that the dielectric mask is etched at a higher rate than the passivation layer, whereby portions of the passivation layer deposited on the dielectric mask are lifted off from the substrate; and depositing a metal layer on the substrate including over the remaining passivation layer and exposed portions of the features.

FIG. 10